

General Description

This PAN20T15X N-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent $R_{ds}(On)$ performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

BVDSS	R _{DS(on)}	I _D
150V	88 mΩ	20A

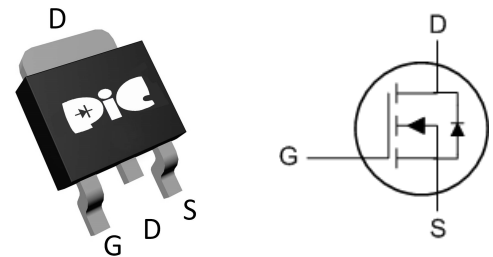
Feature

- ◆ Super Low Gate Charge
- ◆ 100% EAS Guaranteed
- ◆ Green Device Available
- ◆ Excellent CdV/dt effect decline
- ◆ Advanced high cell density Trench technology

Application

- ▼ DC/DC Primary Side Switch
- ▼ Industrial Synchronous
- ▼ Rectification Load Switch
- ▼ DC/DC Converters

TO252 Pin Configuration



Absolute Maximum Ratings(TC=25°C)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current, V_{GS} @ 10V ₁	$I_{D@T_C=25^{\circ}C}$	20	A
Continuous Drain Current, V_{GS} @ 10V ₁	$I_{D@T_C=100^{\circ}C}$	14	A
Continuous Drain Current, V_{GS} @ 10V ₁	$I_{D@T_A=25^{\circ}C}$	3	A
Continuous Drain Current, V_{GS} @ 10V ₁	$I_{D@T_A=70^{\circ}C}$	2.5	A
Pulsed Drain Current ₂	I_{DM}	40	A
Single Pulse Avalanche Energy ₃	EAS	53	mJ
Avalanche Current	I_{AS}	18	A
Total Power Dissipation ₃	$P_{D@T_C=25^{\circ}C}$	72.6	W
Total Power Dissipation ₃	$P_{D@T_A=25^{\circ}C}$	2.1	W
Storage Temperature Range	T_{STG}	-55 to 150	°C
Operating Junction Temperature Range	T_J	-55 to 150	°C
Thermal Resistance Junction-ambient ₁	$R_{\theta JA}$	60	°C/W
Thermal Resistance Junction-Case ₁	$R_{\theta JC}$	1.72	°C/W

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	150	---	---	V
Static Drain-Source On-Resistance ²	R _{DS(ON)}	V _{GS} =10V, I _D =10A	---	---	88	mΩ
Static Drain-Source On-Resistance ²		V _{GS} =4.5V, I _D =10A	---	---	100	mΩ
Gate Threshold Voltage	V _{GS(th)}	V _{GS} =V _{DS} , I _D =250uA	1.2	---	2.5	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =120V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =120V, V _{GS} =0V, T _J =55°C	---	---	5	
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
Forward Transconductance	g _{fs}	V _{DS} =5V, I _D =10A	---	33	---	S
Total Gate Charge	Q _g	V _{DS} =75V, V _{GS} =4.5V, I _D =10A	---	25.1	---	nC
Gate-Source Charge	Q _{gs}		---	6.8	---	
Gate-Drain Charge	Q _{gd}		---	12.6	---	
Turn-On Delay Time	T _{d(on)}	V _{DD} =75V, V _{GS} =10V, R _G =3.3 I _D =10A	---	13	---	ns
Rise Time	T _r		---	8.2	---	
Turn-Off Delay Time	T _{d(off)}		---	25	---	
Fall Time	T _f		---	11	---	
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f=1MHz	---	2285	---	pF
Output Capacitance	C _{oss}		---	110	---	
Reverse Transfer Capacitance	C _{rss}		---	83	---	

Diode Characteristics

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Continuous Source Current ^{1,5}	I _S	V _G =V _D =0V, Force Current	---	---	20	A
Pulsed Source Current ^{2,5}	I _{SM}		---	---	40	A
Diode Forward Voltage ²	V _{SD}	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V
Reverse Recovery Time	t _{rr}	I _F =10A, dI/dt=100A/μs, T _J =25°C	---	37	---	nS
Reverse Recovery Charge	Q _{rr}		---	263	---	nC

Note :

1. Pulse width limited by maximum junction temperature.
2. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
3. The EAS data shows Max. rating. The test condition is V_{DD}=25V, V_{GS}=10V, L=0.3mH, I_{AS}=18A
4. Ensure that the channel temperature does not exceed 150°C.
5. The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

Typical Characteristics

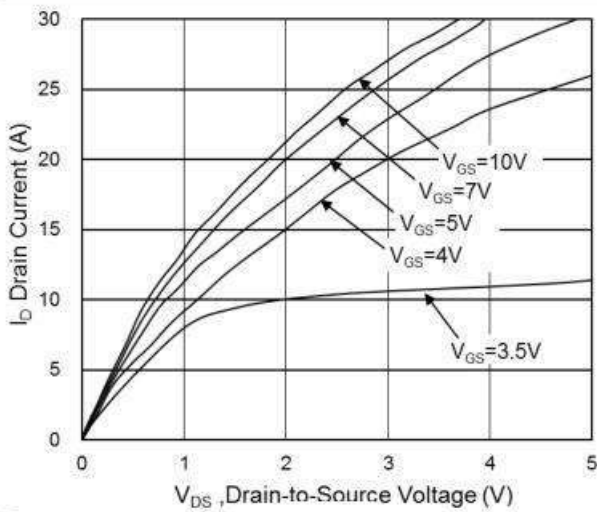


Fig.1 Typical Output Characteristics

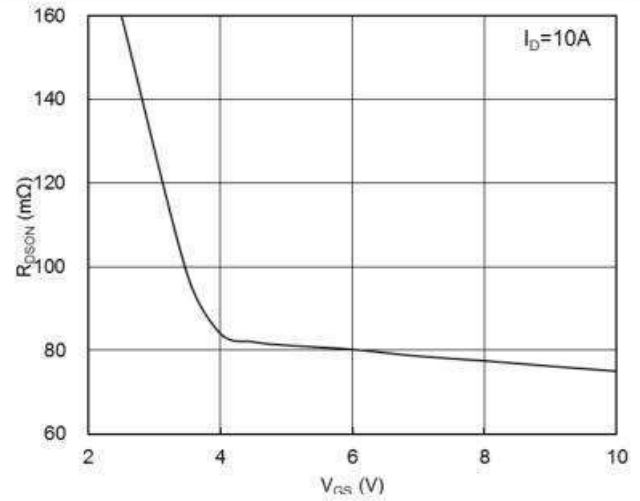


Fig.2 On-Resistance vs. Gate-Source Voltage

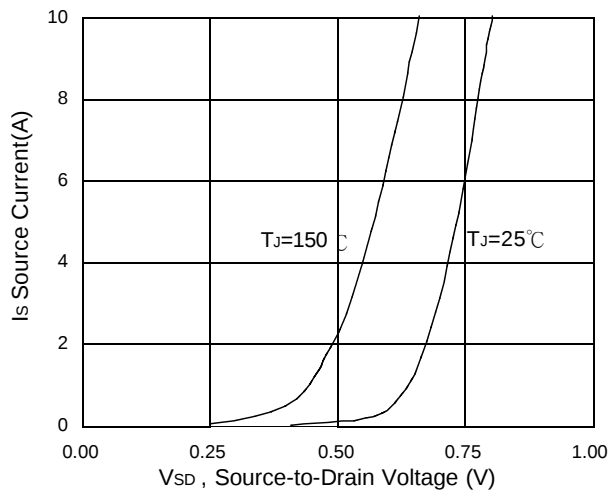


Fig.3 Forward Characteristics of Reverse

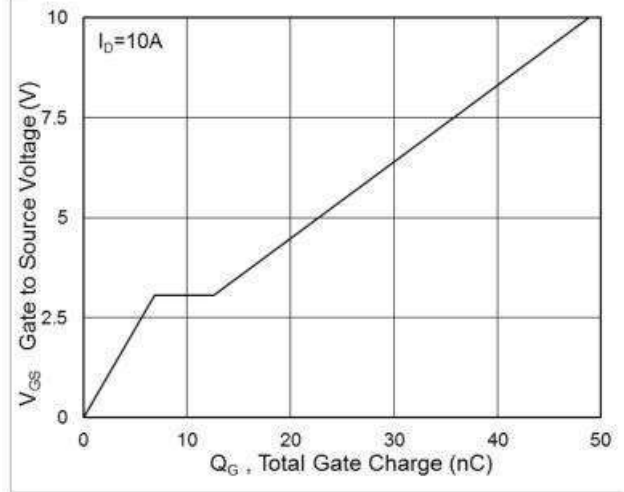


Fig.4 Gate-Charge Characteristics

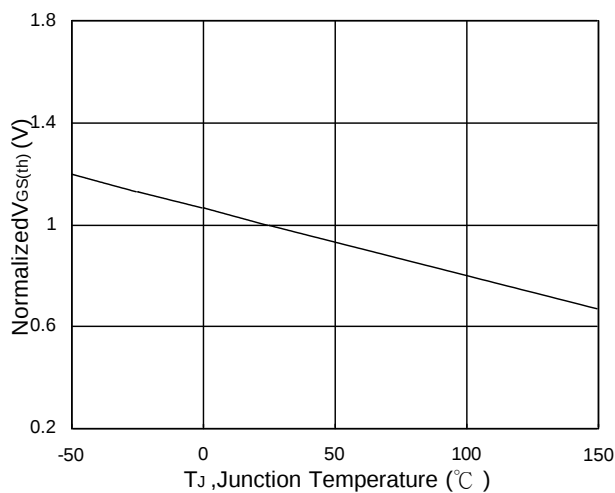


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

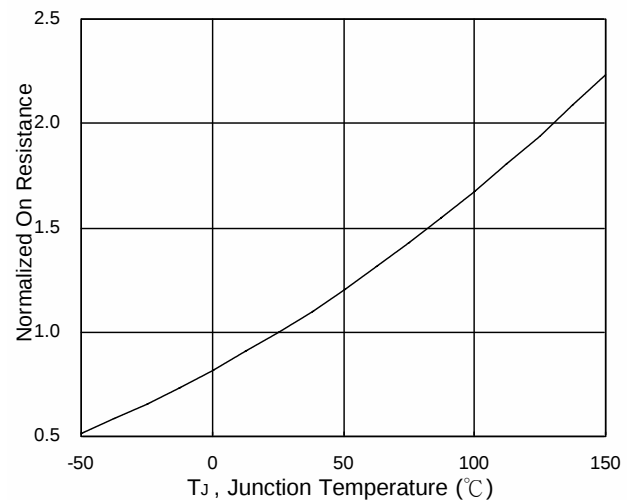


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

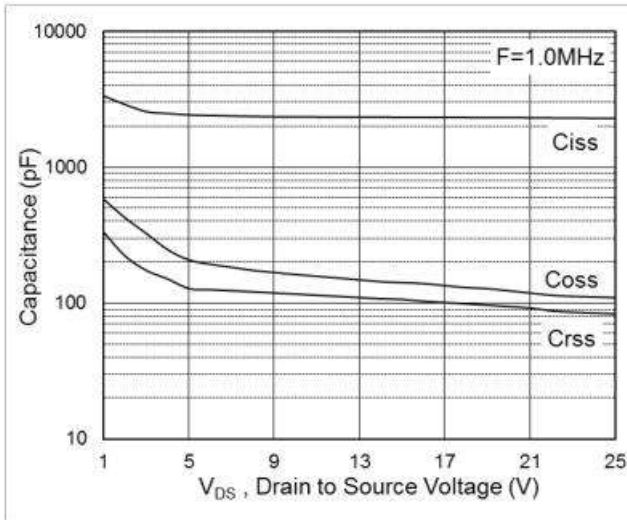


Fig.7 Capacitance

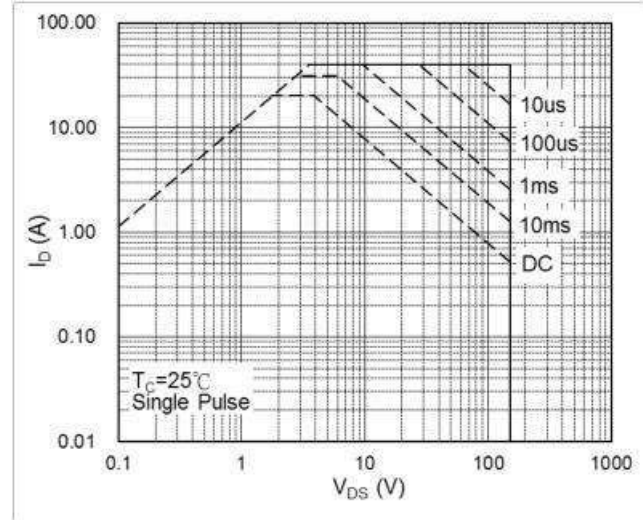


Fig.8 Safe Operating Area

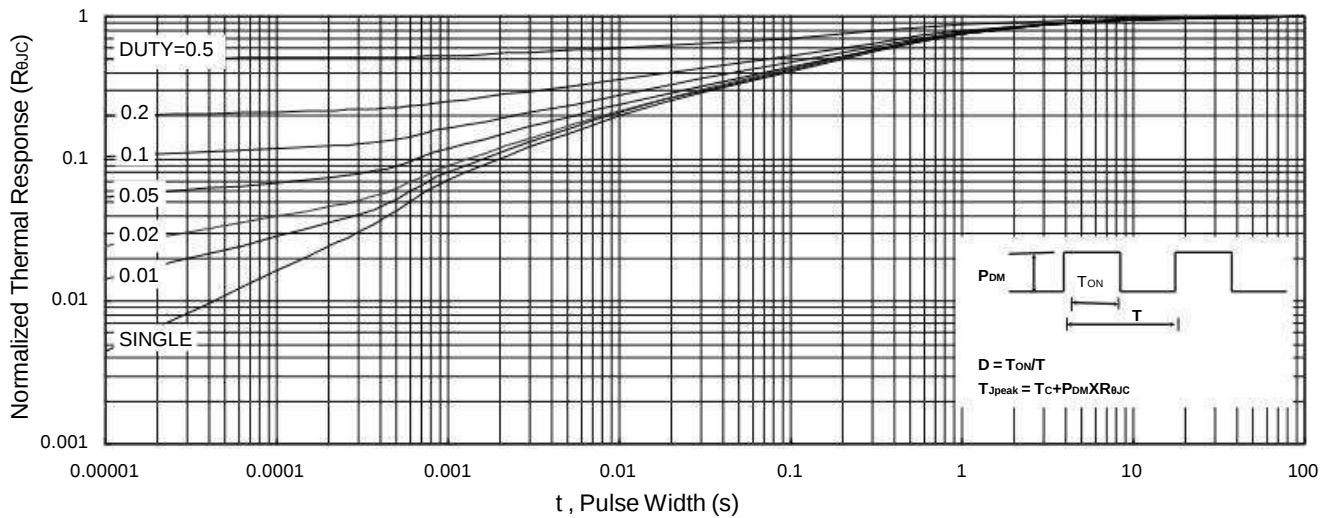


Fig.9 Normalized Maximum Transient Thermal Impedance

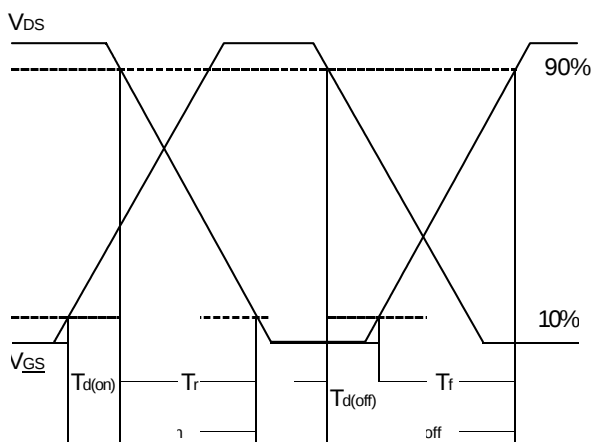


Fig.10 Switching Time Waveform

$$EAS = \frac{1}{2} L \times I_{AS}^2 \times \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$

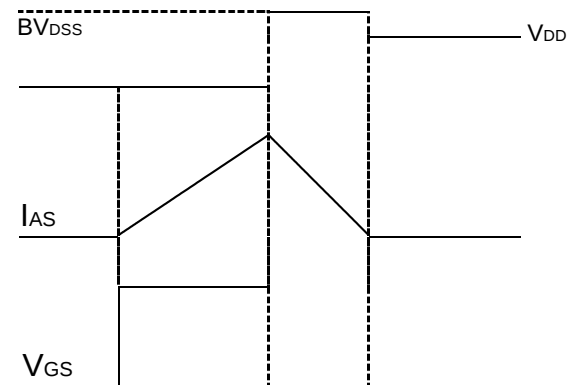
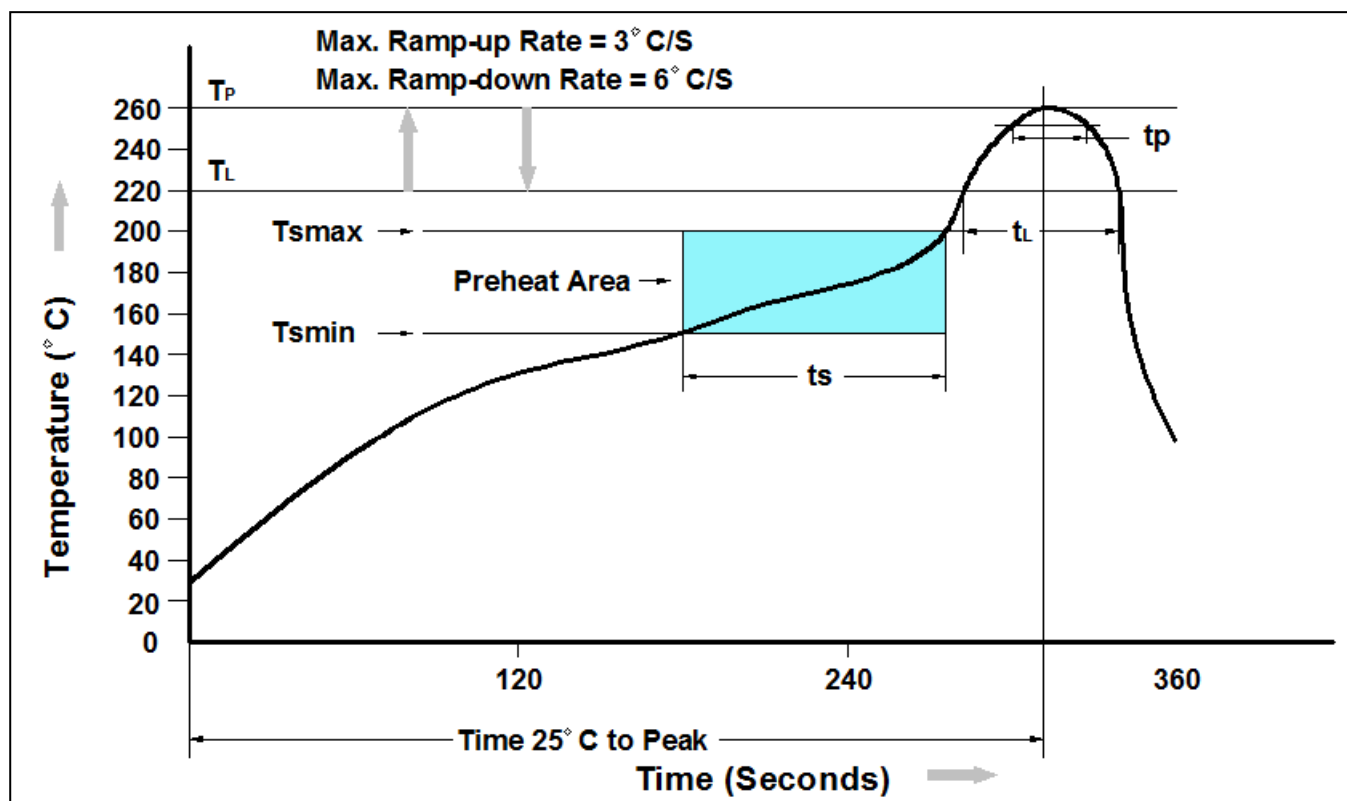


Fig.11 Unclamped Inductive Switching Waveform

Recommmend IR Reflow Soldering Thermal Profile

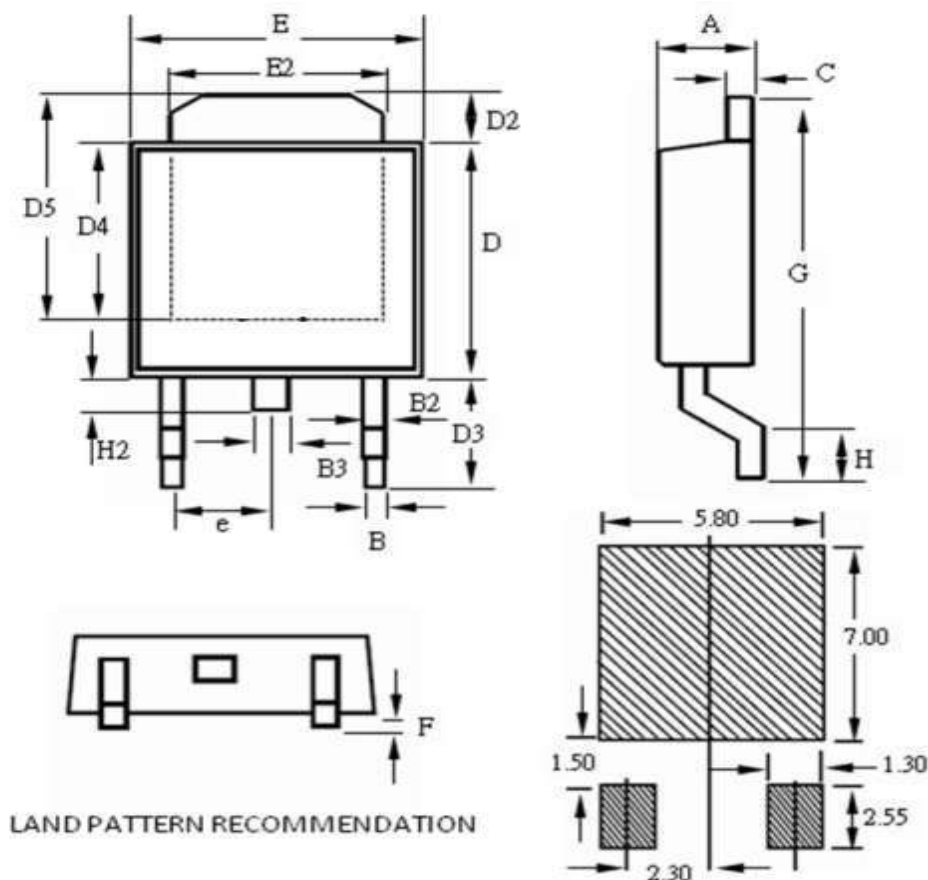


Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (ts) from (Tsmmin to Tsmax)	60-120 seconds
Average Ramp-up Rate (tL to tP)	3°C/second max.
Liquidous Temperature (TL)	217°C
Time (tL) Maintained Above (TL)	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time (tP) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate (TP to TL)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

Ordering Information

Part Number	Description	Quantity
PAN20T15X	TO-252 Reel	2500 pcs

TO-252 Package Outline



SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	2.10	--	2.50	0.083	--	0.098
B	0.30	--	0.89	0.012	--	0.035
B2	0.40	--	1.14	0.016	--	0.045
B3	0.60	--	1.00	0.024	--	0.039
C	0.40	--	0.89	0.016	--	0.035
D	5.30	--	6.25	0.209	--	0.246
D2	0.50	--	1.70	0.020	--	0.067
D3	2.20	--	3.40	0.087	--	0.134
D4	4.32	--	--	0.170	--	--
D5	5.21	--	--	0.205	--	--
E	6.30	--	6.73	0.248	--	0.265
E2	4.80	--	5.46	0.189	--	0.215
F	0.00	--	0.30	0.000	--	0.012
G	9.20	--	10.41	0.362	--	0.410
H	0.90	--	1.95	0.035	--	0.077
H2	0.50	--	1.10	0.020	--	0.043
e	--	2.30	--	--	0.091	--

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